

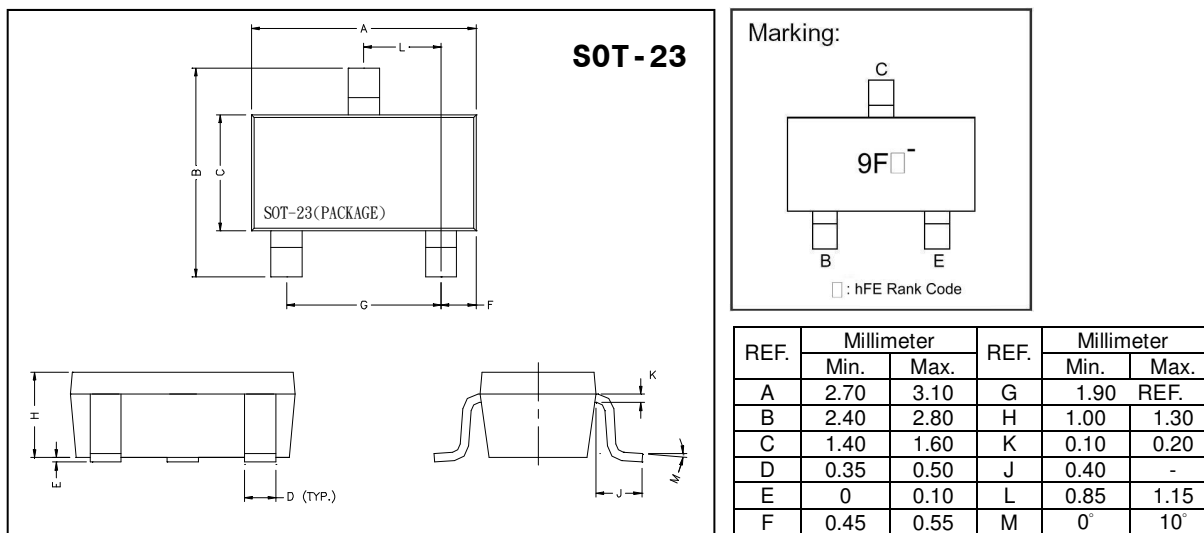
GBC807

PNP EPITAXIAL PLANAR TRANSISTOR

Description

The GBC807 is designed for switching and AF amplifier application, suitable for driver storages and low power output storages.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Collector to Base Voltage	VCBO	-50	V
Collector to Emitter Voltage	VCEO	-45	V
Emitter to Base Voltage	VEBO	-5	V
Collector Current	I _C	-800	mA
Total Power Dissipation	PD	225	mW

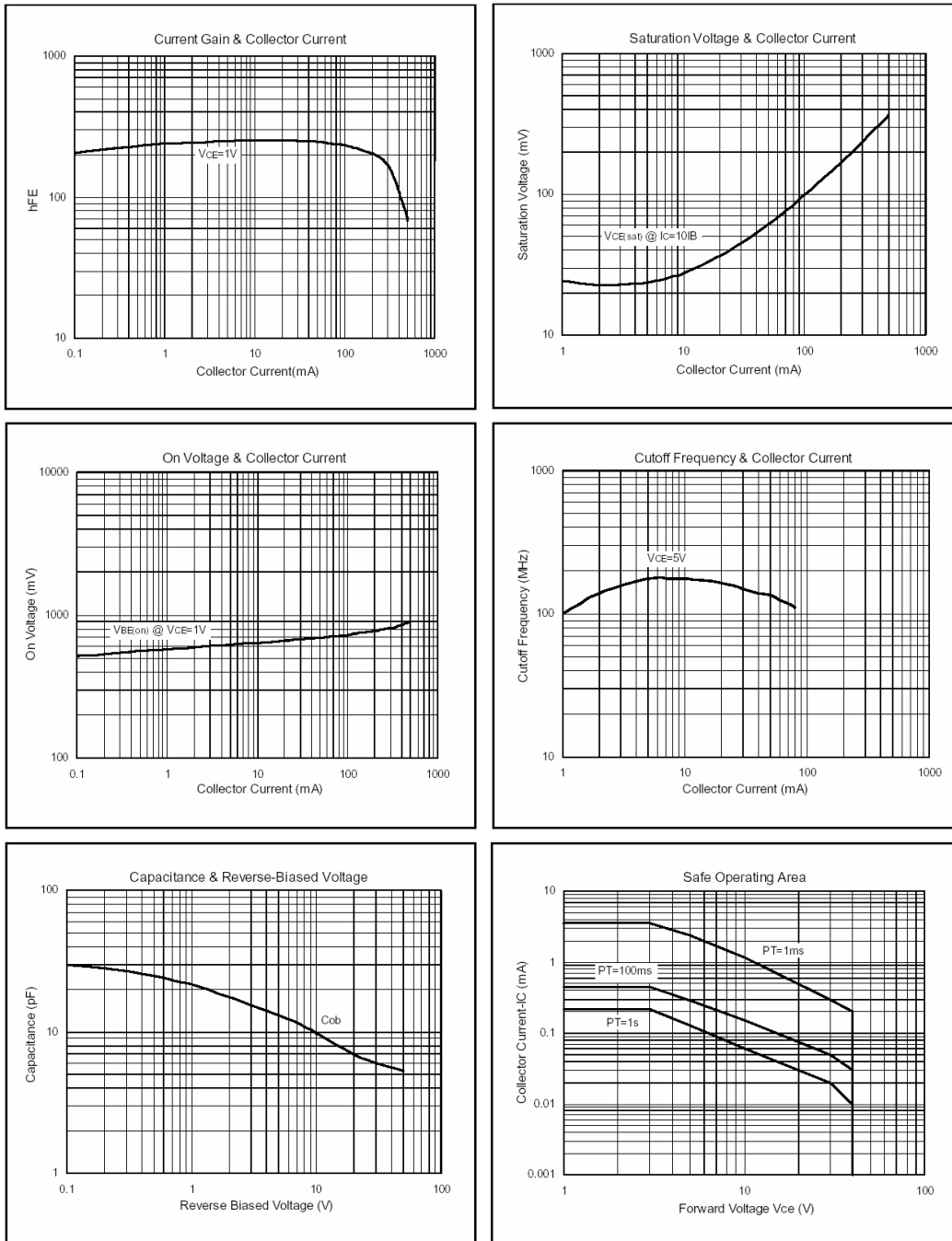
Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVEBO	-5	-	-	V	I _E =-100uA
BVCEO	-45	-	-	V	I _C =-10mA
BVCES	-50	-	-	V	I _C =-100uA
ICES	-	-	-100	nA	V _{CE} =-25V
IEBO	-	-	-100	nA	V _{EB} =-4V
*VCE(sat)	-	-	-700	mV	I _C =-500mA, I _B =-50mA
VBE(on)	-	-	-1.2	V	V _{CE} =-1V, I _C =-300mA
hFE	100	-	630		V _{CE} =-1V, I _C =-100mA
f _T	-	100	-	MHz	V _{CE} =-5V, I _C =-10mA, f=100MHz
C _{ob}	-	-	12	pF	V _{CB} =-10V, f=1MHz, I _E =0A

Classification Of hFE

Rank	A	B	C
hFE	100-250	160-400	250-630

Characteristics Curve



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